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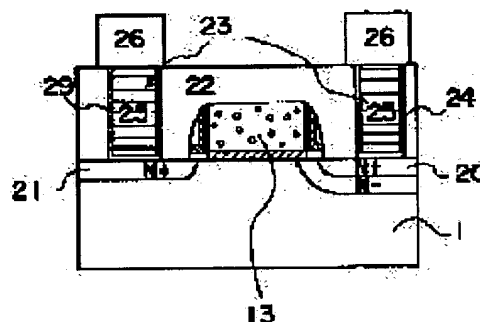
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(54) SEMICONDUCTOR DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a nonvolatile semiconductor device which can be micronized in size and enhanced in reliability, dispensing with a selection transistor.

SOLUTION: A nonvolatile semiconductor memory device is composed of a second conductivity-type first diffusion layer 20, a second conductivity-type second diffusion layer 21, and a gate electrode formed on a part of a channel region located between the diffusion layers 20, 21 and on a part of the first diffusion layer through of a first insulating film, wherein a part of a second insulating film of at least two-layered structure formed on the channel region between the gate electrode and the second diffusion layer 21 of 30nm or less in thickness is made to serve as a charge storage layer.



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